

74AUP1GU04

Low-power unbuffered inverter

Rev. 5 — 29 June 2012

Product data sheet

1. General description

The 74AUP1GU04 provides the single unbuffered inverting gate.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- ESD protection:
 - ◆ HBM JESD22-A114F Class 3A exceeds 5000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Multiple package options
- Specified from $-40^{\circ}C$ to $+85^{\circ}C$ and $-40^{\circ}C$ to $+125^{\circ}C$

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP1GU04GW	$-40^{\circ}C$ to $+125^{\circ}C$	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74AUP1GU04GM	$-40^{\circ}C$ to $+125^{\circ}C$	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body $1 \times 1.45 \times 0.5$ mm	SOT886
74AUP1GU04GF	$-40^{\circ}C$ to $+125^{\circ}C$	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body $1 \times 1 \times 0.5$ mm	SOT891
74AUP1GU04GN	$-40^{\circ}C$ to $+125^{\circ}C$	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115
74AUP1GU04GS	$-40^{\circ}C$ to $+125^{\circ}C$	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202
74AUP1GU04GX	$-40^{\circ}C$ to $+125^{\circ}C$	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm	SOT1226



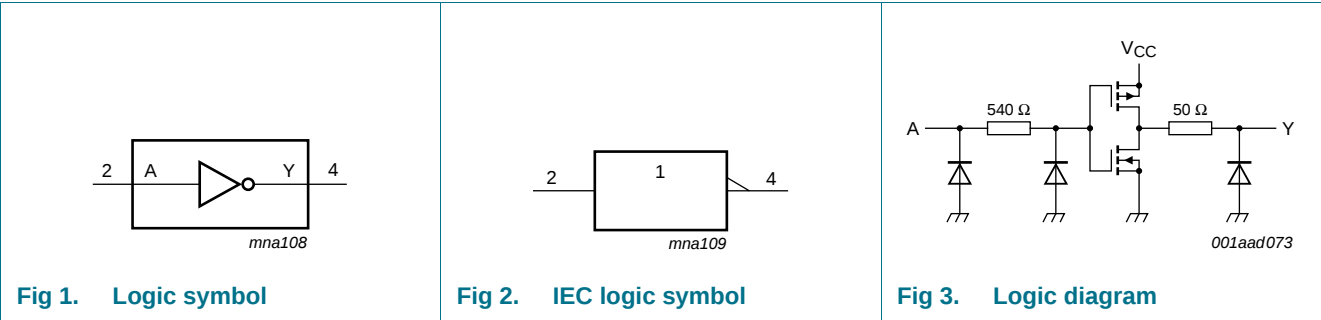
4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74AUP1GU04GW	pD
74AUP1GU04GM	pD
74AUP1GU04GF	pD
74AUP1GU04GN	pD
74AUP1GU04GS	pD
74AUP1GU04GX	pD

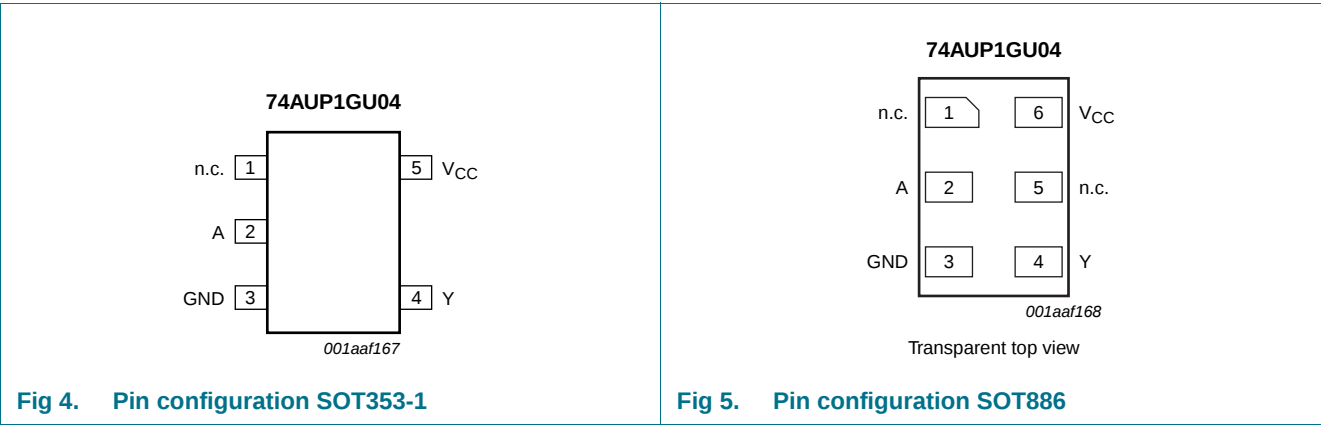
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



74AUP1GU04

n.c. 1 6 V_{CC}
A 2 5 n.c.
GND 3 4 Y
001aaf169
Transparent top view

Fig 6. Pin configuration SOT891, SOT1115 and SOT1202

74AUP1GU04

n.c. 1 5 V_{CC}
A 2 4 Y
3 GND
aaa-003014
Transparent top view

Fig 7. Pin configuration SOT1226 (X2SON5)

6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	TSSOP5 and X2SON5	XSON6	
n.c.	1	1	not connected
A	2	2	data input
GND	3	3	ground (0 V)
Y	4	4	data output
n.c.	-	5	not connected
V _{CC}	5	6	supply voltage

7. Functional description

Table 4. Function table^[1]

Input	Output
A	Y
L	H
H	L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I_{IK}	input clamping current	$V_I < 0$ V	-50	-	mA
V_I	input voltage		^[1] -0.5	+4.6	V
I_{OK}	output clamping current	$V_O < 0$ V	-50	-	mA
V_O	output voltage		^[1] -0.5	$V_{CC} + 0.5$	V
I_O	output current	$V_O = 0$ V to V_{CC}	-	± 20	mA
I_{CC}	supply current		-	+50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	^[2] -	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP5 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.

For XSON6 and X2SON5 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		0.8	3.6	V
V_I	input voltage		0	3.6	V
V_O	output voltage		0	V_{CC}	V
T_{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 0.8$ V to 3.6 V	0	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V to 3.6 V	0.75 × V _{CC}	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V to 3.6 V	-	-	0.25 × V _{CC}	V
V _{OH}	HIGH-level output voltage	I _O = -20 µA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.75 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.11	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.32	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	2.05	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.72	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.6	-	-	V
V _{OL}	LOW-level output voltage	I _O = 20 µA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.44	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.1	µA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.5	µA
C _I	input capacitance	V _{CC} = 0 V to 3.6 V; V _I = GND or V _{CC}	-	1.5	-	pF
C _O	output capacitance	V _O = GND; V _{CC} = 0 V	-	1.8	-	pF
T_{amb} = -40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V to 3.6 V	0.75 × V _{CC}	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V to 3.6 V	-	-	0.25 × V _{CC}	V
V _{OH}	HIGH-level output voltage	I _O = -20 µA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.7 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.03	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.30	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	1.97	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.85	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.67	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.55	-	-	V

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{OL}	LOW-level output voltage	I _O = 20 µA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.33	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.45	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.5	µA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.9	µA
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V to 3.6 V	0.75 × V _{CC}	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V to 3.6 V	-	-	0.25 × V _{CC}	V
V _{OH}	HIGH-level output voltage	I _O = -20 µA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.11	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.6 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	0.93	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.17	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	1.77	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.67	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.40	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.30	-	-	V
V _{OL}	LOW-level output voltage	I _O = 20 µA; V _{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.36	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.50	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.75	µA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	1.4	µA

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#)

Symbol	Parameter	Conditions	25 °C			−40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pF									
t _{pd}	propagation delay	A to Y; see Figure 8	[2]						
		V _{CC} = 0.8 V	-	6.2	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	0.9	2.3	4.4	0.9	4.8	5.3	ns
		V _{CC} = 1.4 V to 1.6 V	0.7	1.7	3.1	0.6	3.4	3.8	ns
		V _{CC} = 1.65 V to 1.95 V	0.5	1.4	2.6	0.5	2.9	3.2	ns
		V _{CC} = 2.3 V to 2.7 V	0.4	1.1	2.0	0.4	2.3	2.6	ns
		V _{CC} = 3.0 V to 3.6 V	0.3	1.0	1.8	0.3	2.1	2.4	ns
C _L = 10 pF									
t _{pd}	propagation delay	A to Y; see Figure 8	[2]						
		V _{CC} = 0.8 V	-	9.6	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	1.2	3.1	6.1	1.2	6.8	7.5	ns
		V _{CC} = 1.4 V to 1.6 V	1.0	2.3	4.0	0.9	4.6	5.1	ns
		V _{CC} = 1.65 V to 1.95 V	0.8	1.9	3.3	0.7	3.8	4.2	ns
		V _{CC} = 2.3 V to 2.7 V	0.6	1.5	2.7	0.6	3.1	3.5	ns
		V _{CC} = 3.0 V to 3.6 V	0.5	1.3	2.4	0.5	2.7	3.0	ns
C _L = 15 pF									
t _{pd}	propagation delay	A to Y; see Figure 8	[2]						
		V _{CC} = 0.8 V	-	13.0	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	1.6	3.8	7.9	1.4	8.8	9.7	ns
		V _{CC} = 1.4 V to 1.6 V	1.3	2.8	4.9	1.1	5.7	6.3	ns
		V _{CC} = 1.65 V to 1.95 V	1.0	2.3	4.0	0.9	4.7	5.2	ns
		V _{CC} = 2.3 V to 2.7 V	0.8	1.9	3.2	0.8	3.7	4.1	ns
		V _{CC} = 3.0 V to 3.6 V	0.7	1.6	2.9	0.7	3.3	3.7	ns
C _L = 30 pF									
t _{pd}	propagation delay	A to Y; see Figure 8	[2]						
		V _{CC} = 0.8 V	-	23.2	-	-	-	-	-
		V _{CC} = 1.1 V to 1.3 V	2.4	6.0	13.1	2.2	14.8	16.3	ns
		V _{CC} = 1.4 V to 1.6 V	2.0	4.2	7.6	1.8	9.0	9.9	ns
		V _{CC} = 1.65 V to 1.95 V	1.7	3.6	6.1	1.5	7.2	8.0	ns
		V _{CC} = 2.3 V to 2.7 V	1.4	2.9	4.8	1.3	5.7	6.3	ns
		V _{CC} = 3.0 V to 3.6 V	1.2	2.5	4.3	1.1	5.1	5.7	ns

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#)

Symbol	Parameter	Conditions	25 °C			–40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	

$C_L = 5 \text{ pF}, 10 \text{ pF}, 15 \text{ pF}$ and 30 pF

C_{PD}	power dissipation capacitance	$f = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$ ^[3]							
		$V_{CC} = 0.8 \text{ V}$	-	1.2	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	-	1.1	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	-	1.2	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	-	1.4	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	2.8	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	4.4	-	-	-	-	pF

[1] All typical values are measured at nominal V_{CC} .

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

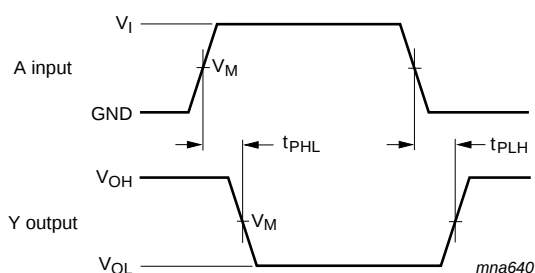
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms



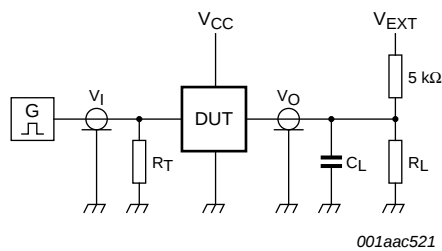
Measurement points are given in [Table 9](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig 8. The data input (A) to output (Y) propagation delays

Table 9. Measurement points

Supply voltage	Output	Input		
V_{CC}	V_M	V_M	V_I	$t_r = t_f$
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V_{CC}	$\leq 3.0 \text{ ns}$



Test data is given in [Table 10](#).
Definitions for test circuit:
 R_L = Load resistance.
 C_L = Load capacitance including jig and probe capacitance.
 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.
 V_{EXT} = External voltage for measuring switching times.

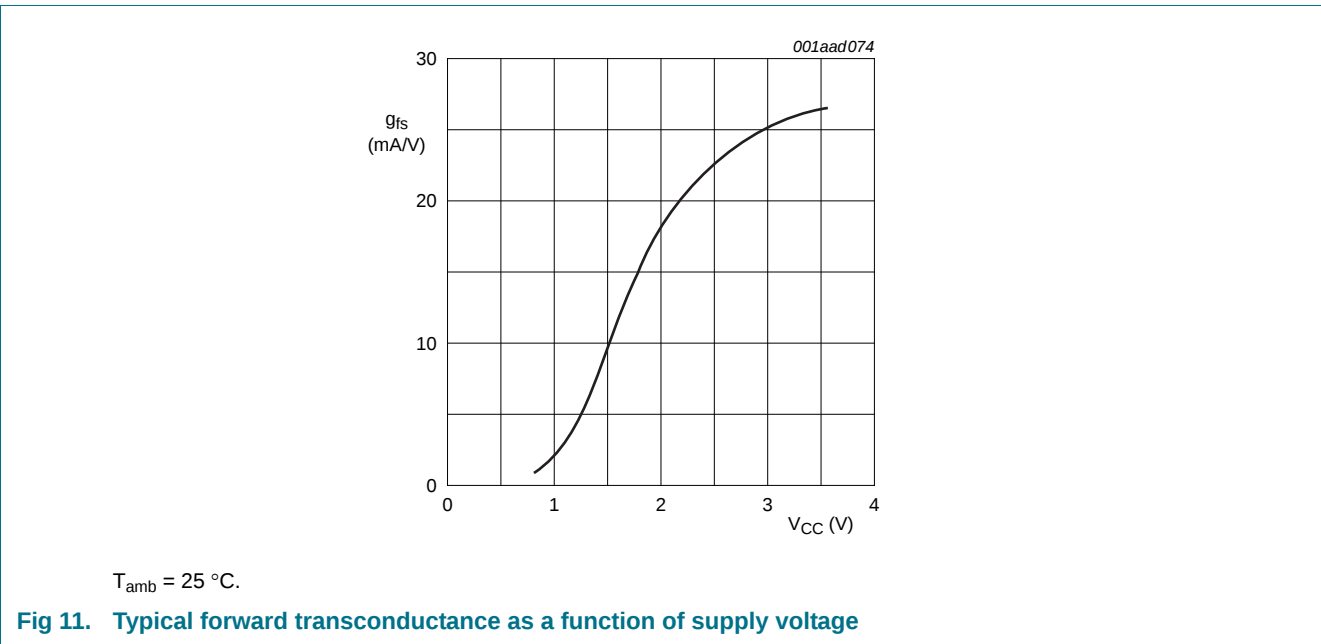
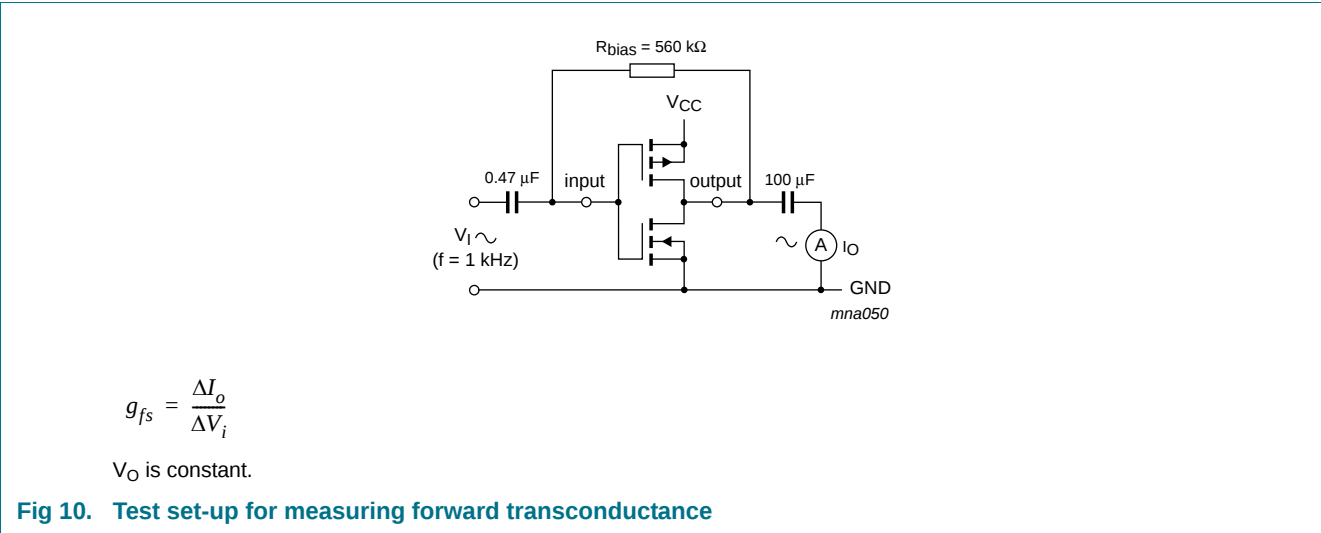
Fig 9. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load		V_{EXT}		
V_{CC}	C_L	R_L [1]	t_{PLH} , t_{PHL}	t_{PZH} , t_{PHZ}	t_{PZL} , t_{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times $R_L = 5 \text{ k}\Omega$, for measuring propagation delays, setup and hold times and pulse width $R_L = 1 \text{ M}\Omega$.

13. Additional characteristics

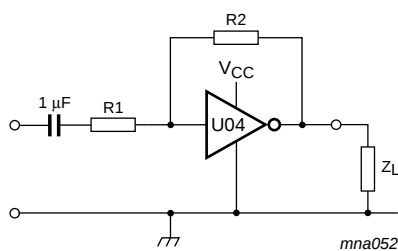


14. Application information

Some applications for the 74AUP1GU04 are:

- Linear amplifier (see [Figure 12](#))
- Crystal oscillator (see [Figure 13](#)).

Remark: All values given are typical values unless otherwise specified.



$Z_L > 10 \text{ k}\Omega$.

$R1 \geq 3 \text{ k}\Omega$.

$R2 \leq 1 \text{ M}\Omega$.

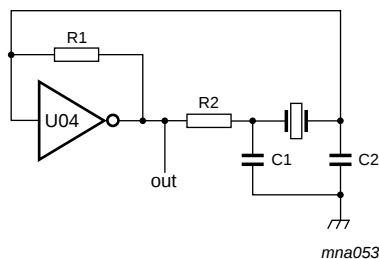
Open loop gain: $G_{OL} = 20$.

$$\text{Voltage amplification: } A_V = -\frac{G_{OL}}{1 + \frac{R1}{R2}(1 + G_{OL})}$$

$V_{o(p-p)} = V_{CC} - 1.5 \text{ V}$ centered at $0.5 \times V_{CC}$.

Unity gain bandwidth product is 5 MHz.

Fig 12. Linear amplifier application



$C1 = 47 \text{ pF}$.

$C2 = 22 \text{ pF}$.

$R1 = 1 \text{ M}\Omega$ to $10 \text{ M}\Omega$.

$R2$ optimum value depends on the frequency and required stability against changes in V_{CC} or average minimum I_{CC} ($I_{CC} = 2 \text{ mA}$ at $V_{CC} = 3.3 \text{ V}$ and $f = 10 \text{ MHz}$).

Fig 13. Crystal oscillator application

15. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1

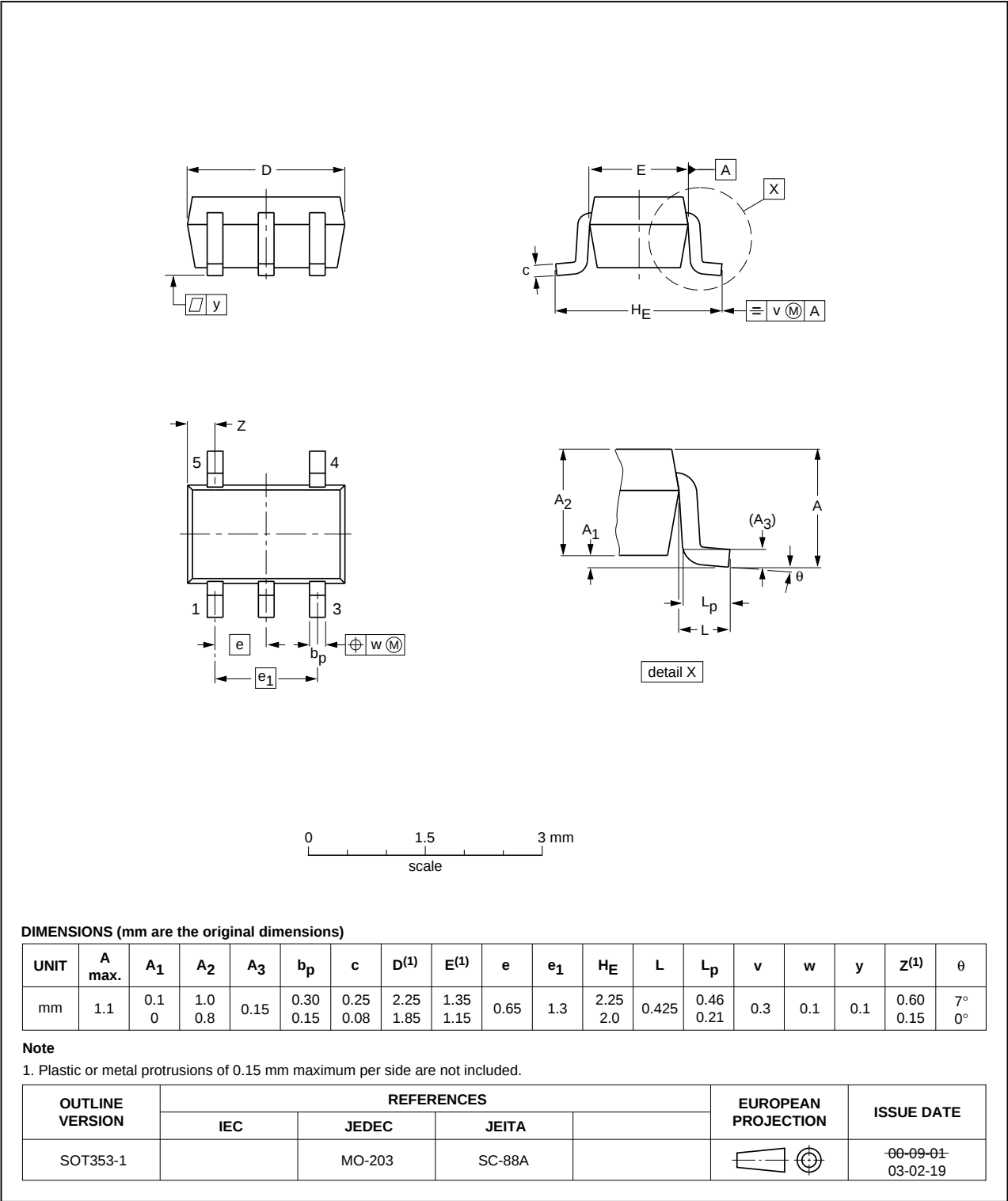


Fig 14. Package outline SOT353-1 (TSSOP5)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

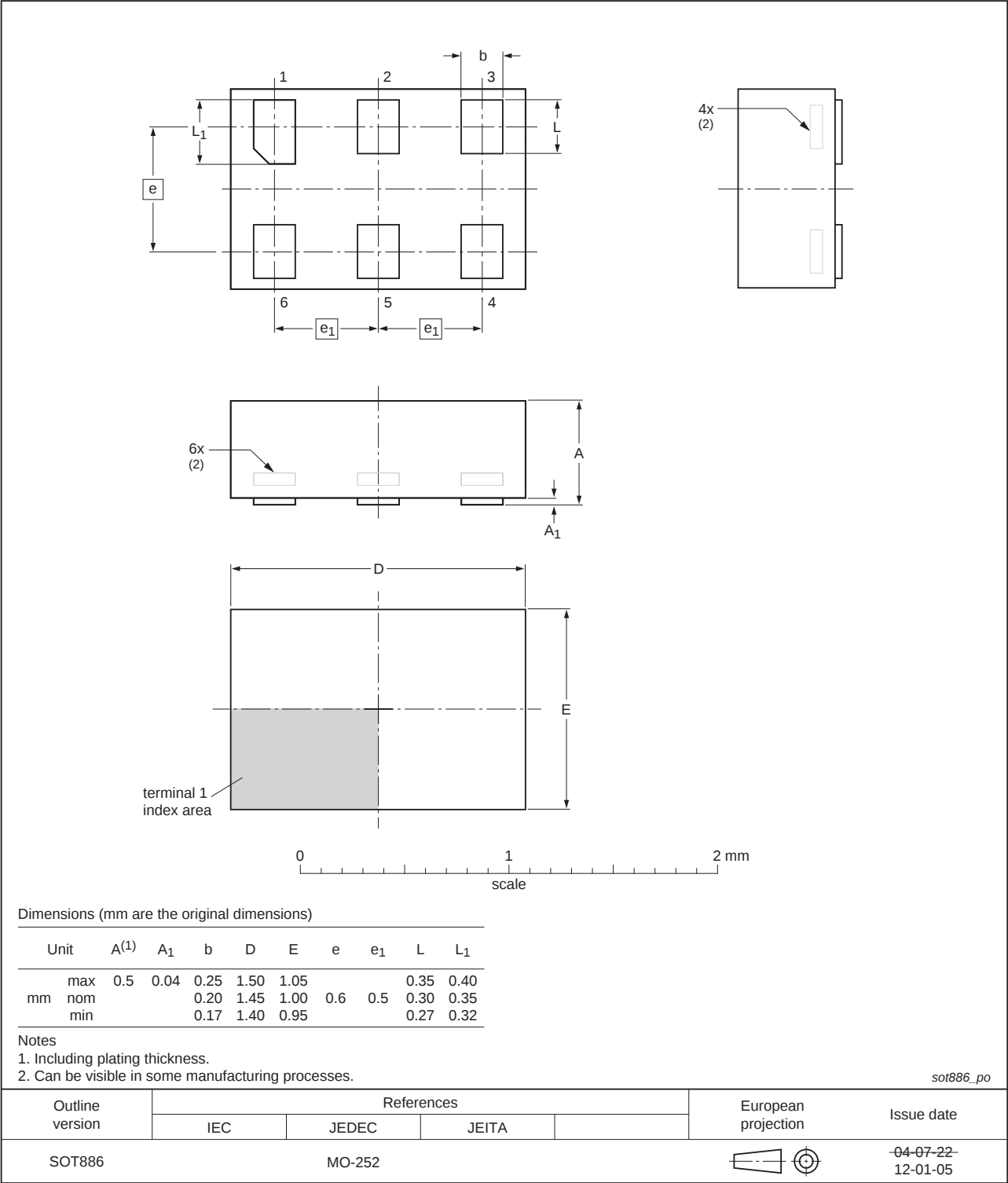


Fig 15. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891

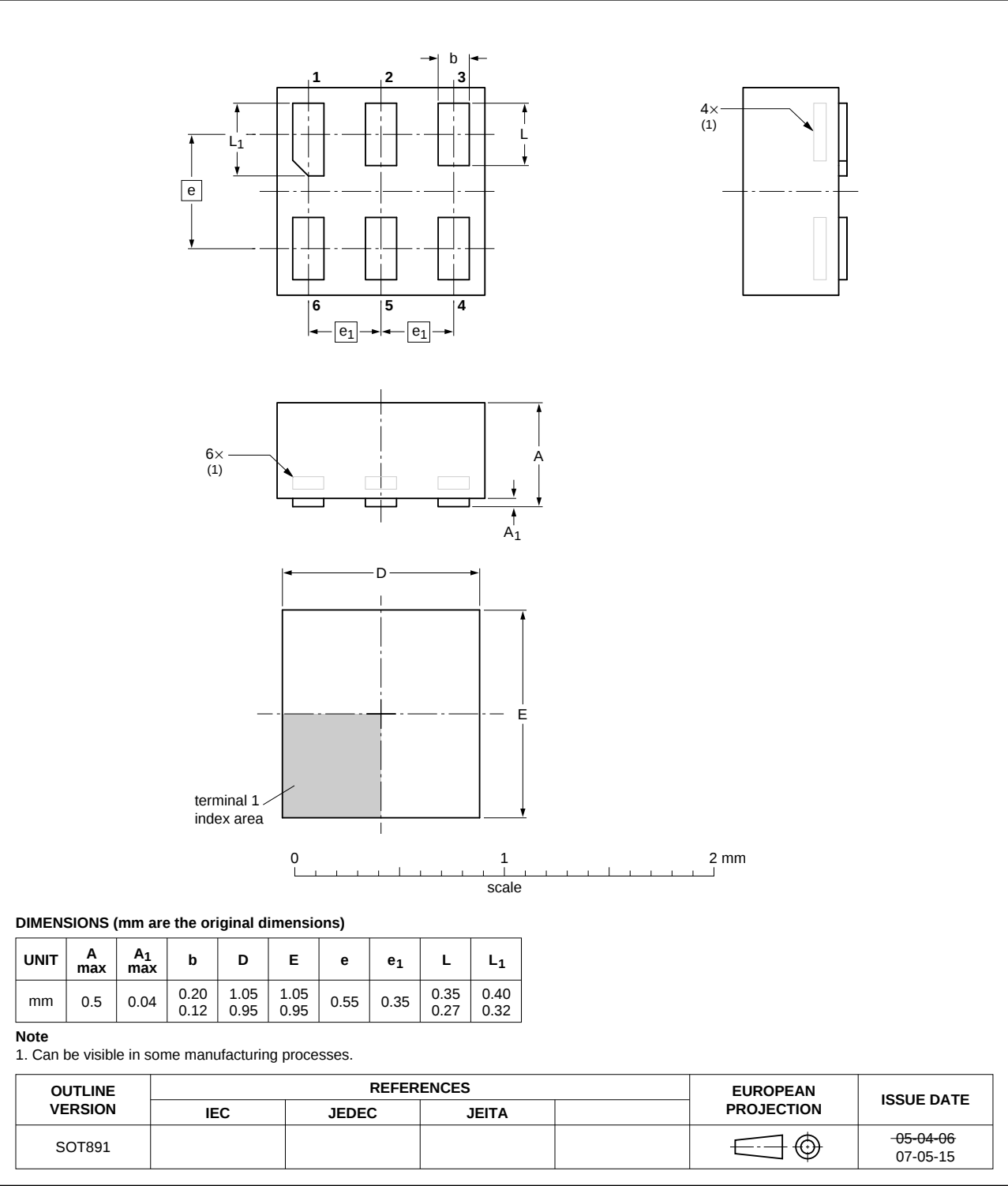
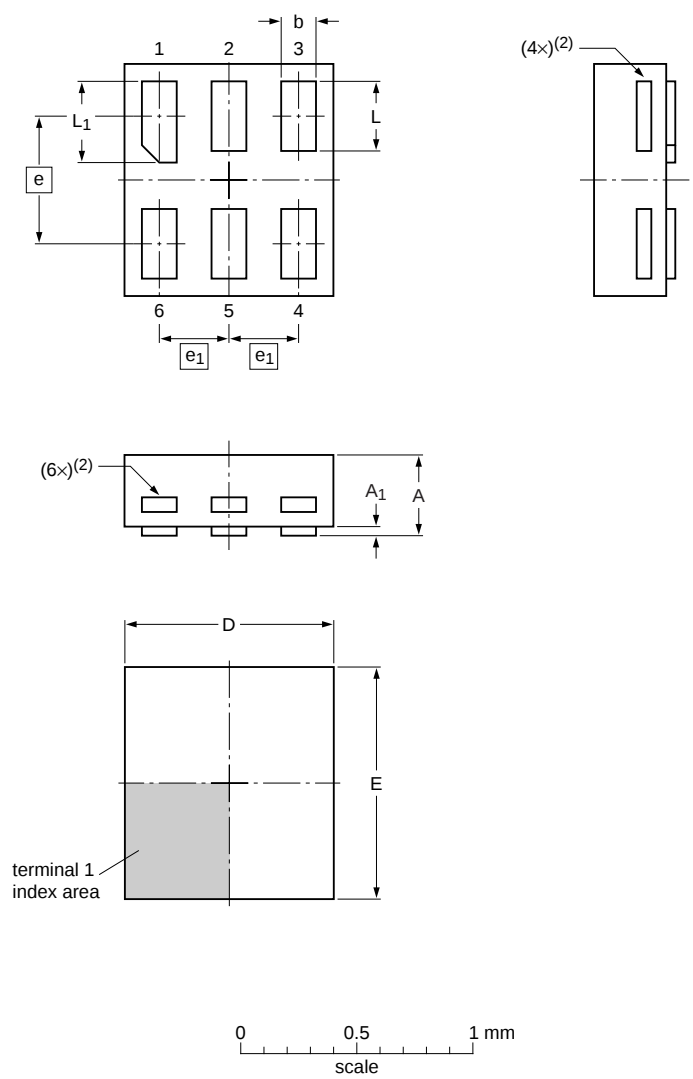


Fig 16. Package outline SOT891 (XSON6)

XSON6: extremely thin small outline package; no leads;
6 terminals; body 0.9 x 1.0 x 0.35 mm

SOT1115



Dimensions

Unit	A ⁽¹⁾	A ₁	b	D	E	e	e ₁	L	L ₁
mm	max	0.35	0.04	0.20	0.95	1.05		0.35	0.40
	nom			0.15	0.90	1.00	0.55	0.30	0.35
	min			0.12	0.85	0.95		0.27	0.32

Note

- 1. Including plating thickness.
- 2. Visible depending upon used manufacturing technology.

sot1115_po

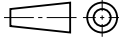
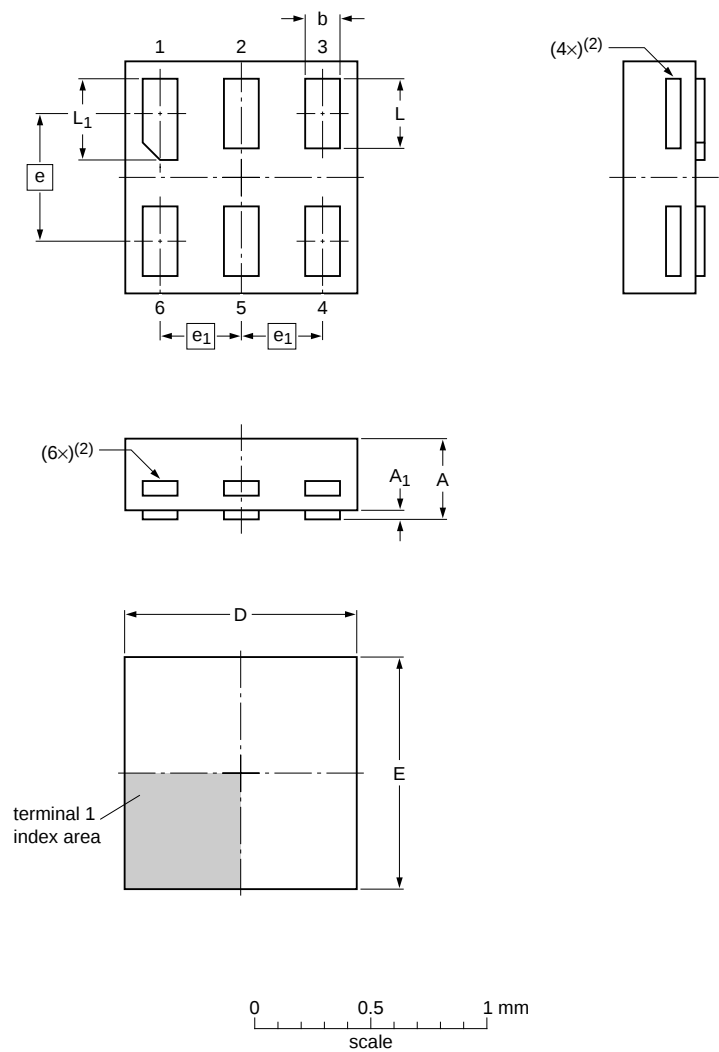
Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1115						10-04-02 10-04-07

Fig 17. Package outline SOT1115 (XSON6)

XSON6: extremely thin small outline package; no leads;
6 terminals; body 1.0 x 1.0 x 0.35 mm

SOT1202



Dimensions

Unit	A ⁽¹⁾	A ₁	b	D	E	e	e ₁	L	L ₁
mm	max	0.35	0.04	0.20	1.05	1.05		0.35	0.40
	nom			0.15	1.00	1.00	0.55	0.30	0.35
	min			0.12	0.95	0.95		0.27	0.32

Note

- 1. Including plating thickness.
- 2. Visible depending upon used manufacturing technology.

sot1202_po

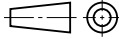
Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1202						10-04-02 10-04-06

Fig 18. Package outline SOT1202 (XSON6)

X2SON5: plastic thermal enhanced extremely thin small outline package; no leads;
5 terminals; body 0.8 x 0.8 x 0.35 mm

SOT1226

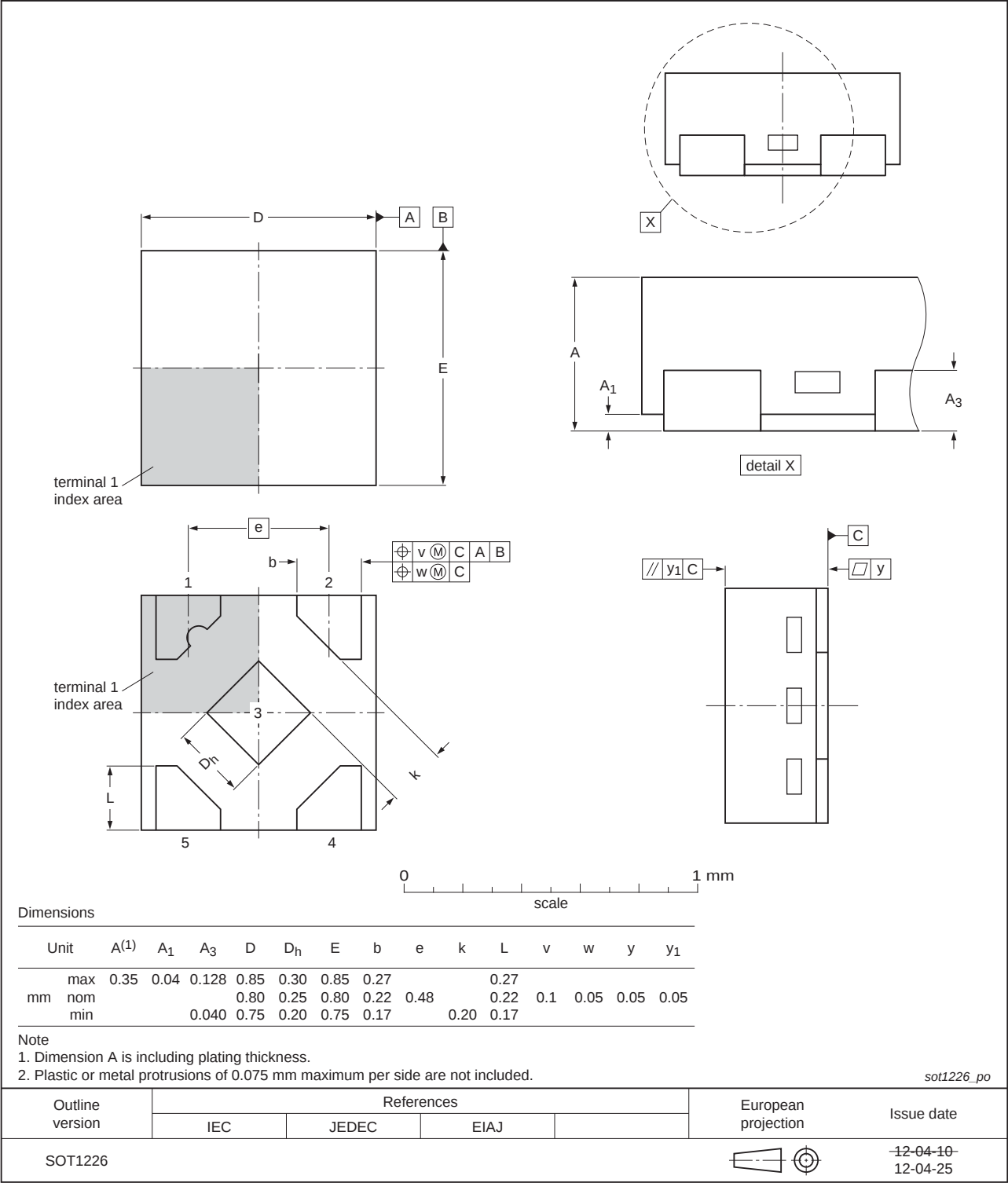


Fig 19. Package outline SOT1226 (X2SON5)

16. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

17. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1GU04 v.5	20120629	Product data sheet	-	74AUP1GU04 v.4
Modifications:	- Added type number 74AUP1GU04GX (SOT1226) - Package outline drawing of SOT886 (Figure 15) modified.			
74AUP1GU04 v.4	20111116	Product data sheet	-	74AUP1GU04 v.3
Modifications:	- Legal pages updated. - Package outline drawing SOT363 replaced by SOT353-1.			
74AUP1GU04 v.3	20100721	Product data sheet	-	74AUP1GU04 v.2
74AUP1GU04 v.2	20060803	Product data sheet	-	74AUP1GU04 v.1
74AUP1GU04 v.1	20050810	Product data sheet	-	-

18. Legal information

18.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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20. Contents

1	General description	1
2	Features and benefits	1
3	Ordering information	1
4	Marking	2
5	Functional diagram	2
6	Pinning information	2
6.1	Pinning	2
6.2	Pin description	3
7	Functional description	3
8	Limiting values	4
9	Recommended operating conditions	4
10	Static characteristics	5
11	Dynamic characteristics	7
12	Waveforms	8
13	Additional characteristics	10
14	Application information	11
15	Package outline	12
16	Abbreviations	18
17	Revision history	18
18	Legal information	19
18.1	Data sheet status	19
18.2	Definitions	19
18.3	Disclaimers	19
18.4	Trademarks	20
19	Contact information	20
20	Contents	21

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